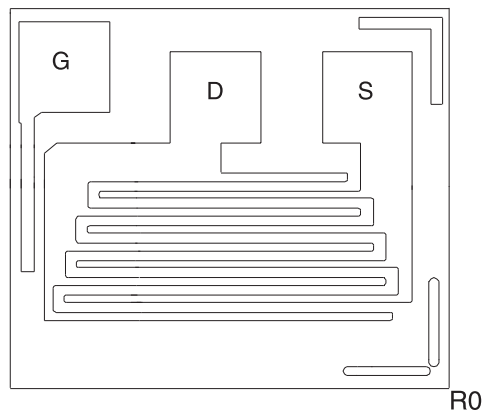


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	21 x 18 MILS
Die Thickness	8.0 MILS
Drain Bonding Pad Area	3.8 X 3.8 MILS
Source Bonding Pad Area	3.8 X 3.8 MILS
Gate Bonding Pad Area	3.8 X 3.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY**BACKSIDE GATE****GROSS DIE PER 4 INCH WAFER**

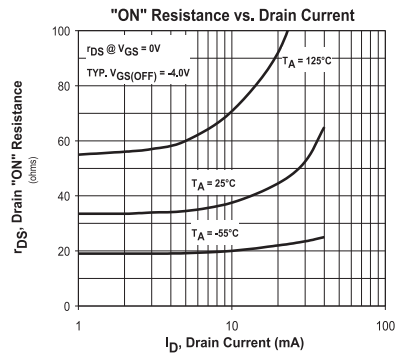
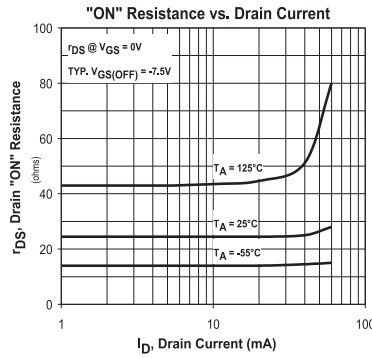
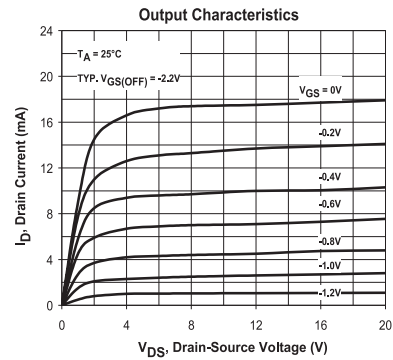
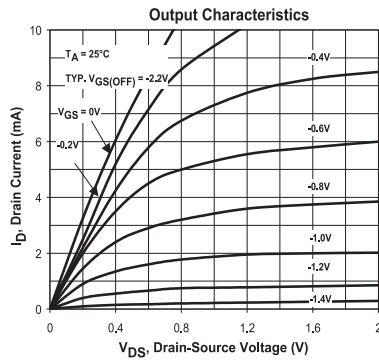
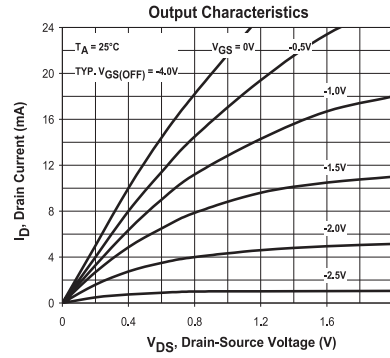
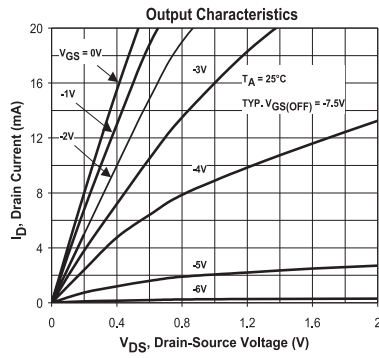
30,950

PRINCIPAL DEVICE TYPES

2N4391
2N4392
2N4393
CMPF4391
CMPF4392
CMPF4393

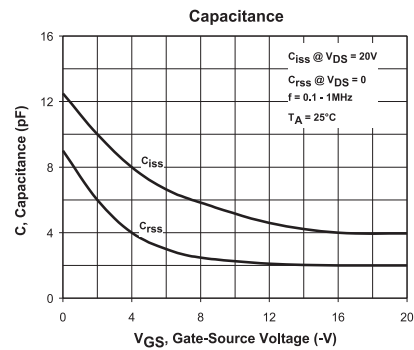
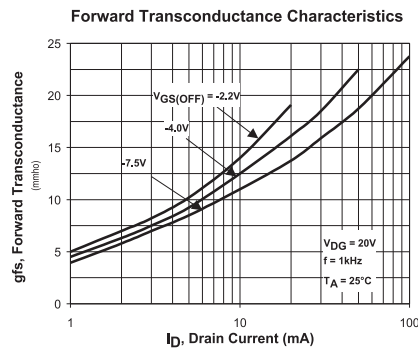
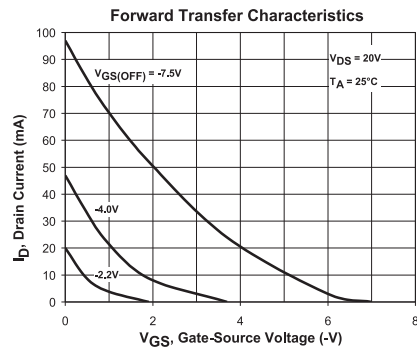
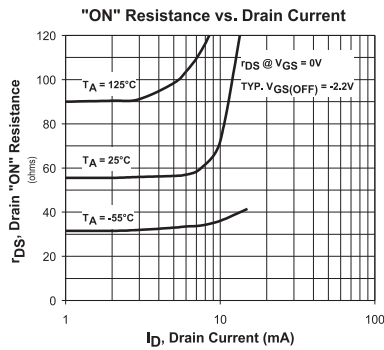
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